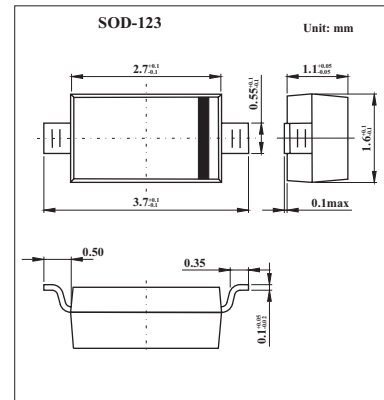


BA782; BA783

■ **Features**

- Silicon Epitaxial Planar Diode Switches
- For high-speed switching application and TV tuners in the frequency range of 50 . . . 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.
- These diodes are also available in SOD-323 case with the type designations BA782S and BA783S.



■ **Absolute Maximum Ratings** Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	35	V
Forward Continuous Current at Tamb = 25°C	I _F	100	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	-55 to +150	°C

■ **Electrical Characteristics** Ta = 25°C

Parameter	Symbol	Min	Typ	Max	Unit
Forward Voltage at I _F = 100 mA	V _(BR)			1	V
Leakage Current at V _R = 20 V	I _R			50	nA
Dynamic Forward Resistance at f = 50 to 1000 MHz, I _F = 3 mA	r _f			0.7	Ω
BA783				1.2	
at f = 50 to 1000 MHz, I _F = 10 mA	r _f			0.5	Ω
BA783				0.9	
Capacitance at V _R = 1 V, f = 1 MHz	C _{tot}			1.5	pF
BA782				1.25	
BA783				1.2	
Series Inductance across Case	L _s		2.5		nH